TAIWAN SEMICONDUCTOR

12A, 600V Ultra Fast Rectifier

FEATURES

- AEC-Q101 qualified available
- High efficiency, Low V_F
- High surge current capability
- High current capability
- High reliability
- Low power loss
- UL Recognized File # E-326243
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- DC to DC converter
- Switching mode converters and inverters
- Freewheeling application

MECHANICAL DATA

- Case: ITO-220AC
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.70g (approximately)

KEY PARAMETERS		
PARAMETER	VALUE	UNIT
I_F	12	A
V_{RRM}	600	V
I_{FSM}	135	A
$T_{J\,MAX}$	150	°C
Package	ITO-220AC	
Configuration	Single die	

ITO-220AC

PIN 1

PIN 2
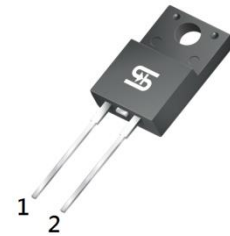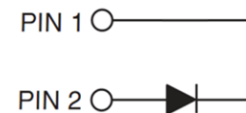
ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

PARAMETER	SYMBOL	UGF12J	UNIT
Marking code on the device		UGF12J	
Repetitive peak revers voltage	V_{RRM}	600	V
Reverse voltage total rms value	$V_{R(RMS)}$	420	V
Forward current	I_F	12	A
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I_{FSM}	135	A
Junction temperature	T_J	-55 to +150	°C
Storage temperature	T_{STG}	-55 to +150	°C

Version: D2105

THERMAL PERFORMANCE

PARAMETER	SYMBOL	TYP	UNIT
Junction-to-case resistance	$R_{\Theta JC}$	4.5	°C/W

ELECTRICAL SPECIFICATIONS (T_A = 25°C unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	TYP	MAX	UNIT
Forward voltage[1]	I_F = 12A, T_J = 25°C	V_F	-	2.0	V
Reverse current @ rated V_R[2]	T_J = 25°C	I_R	-	5	μA
	T_J = 125°C		-	600	μA
Reverse recovery time	I_F = 0.5A, I_R = 1.0A, I_{rr} = 0.25A	t_{rr}	-	20	ns

Notes:

1. Pulse test with PW = 0.3ms
2. Pulse test with PW = 30ms

ORDERING INFORMATION

ORDERING CODE[1]	PACKAGE	PACKING
UGF12J	ITO-220AC	50 / Tube
UGF12JH	ITO-220AC	50 / Tube

Notes:

1. "H" means AEC-Q101 qualified

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CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

Fig.1 Forward Current Derating Curve
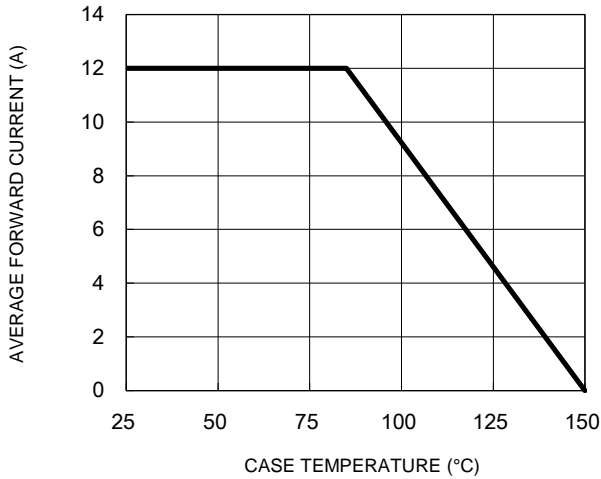
Fig.2 Typical Junction Capacitance

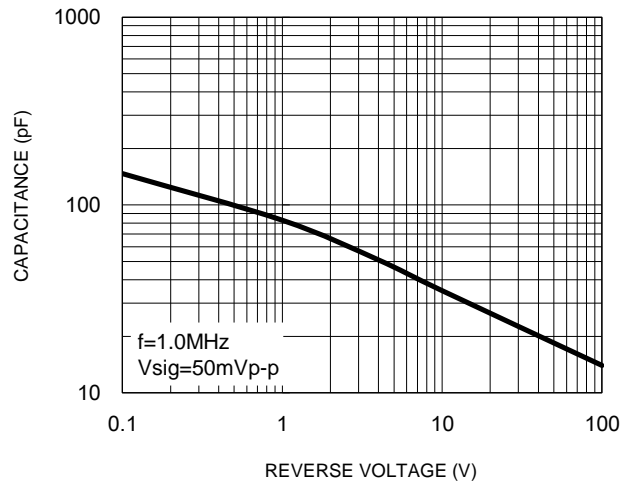f=1.0MHz
Vsig=50mVp-p

Fig.3 Typical Reverse Characteristics

T_J=125°C

T_J=25°C
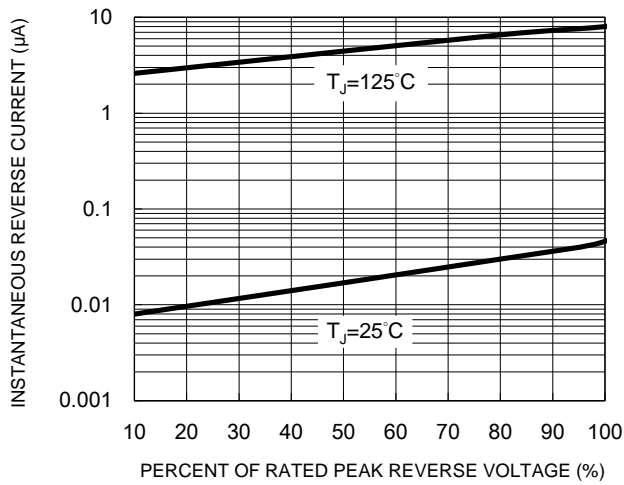
Fig.4 Typical Forward Characteristics

T_J=125°C

T_J=25°C

Pulse width 300μs
1% duty cycle
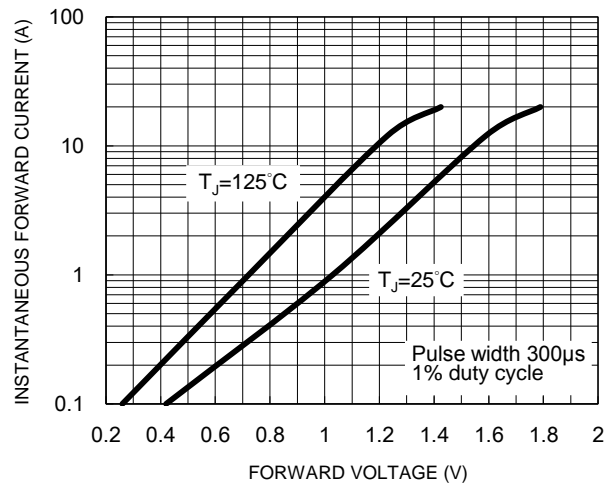
Fig.5 Maximum Non-Repetitive Forward Surge Current

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UGF12J

Taiwan Semiconductor
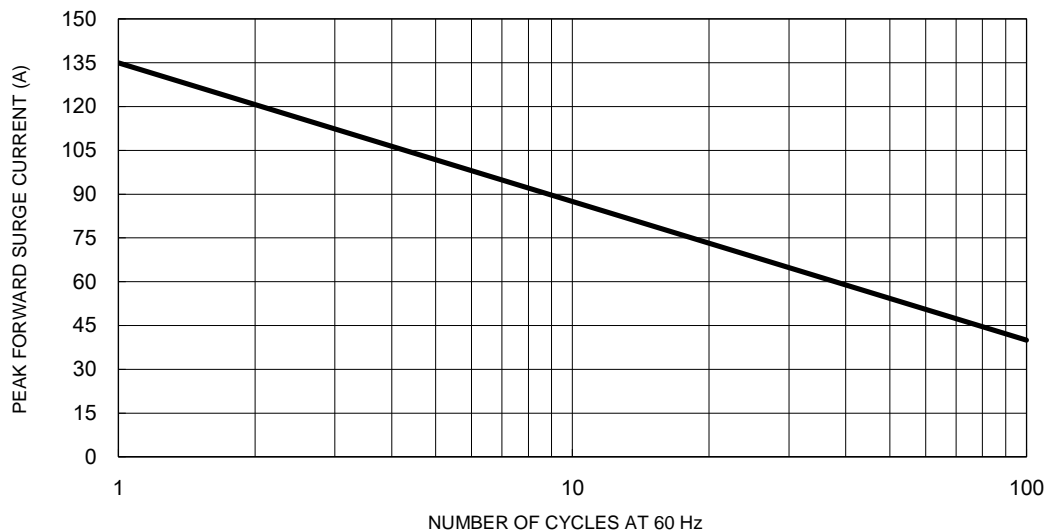
PACKAGE OUTLINE DIMENSIONS

ITO-220AC
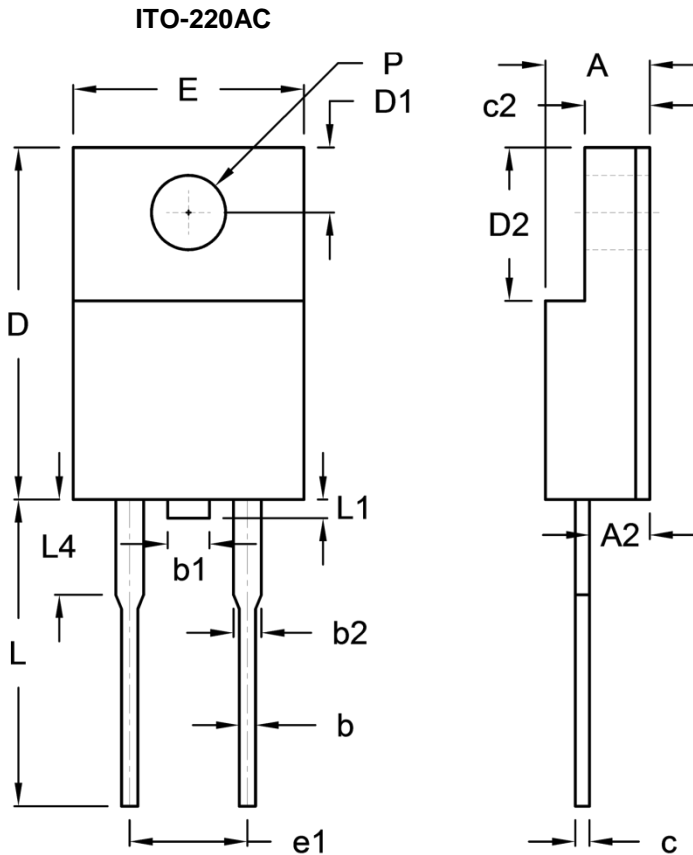
DIM.	Unit (mm)		Unit (inch)	
	Min.	Max.	Min.	Max.
A	4.30	4.70	0.169	0.185
A2	2.30	2.90	0.091	0.114
b	0.50	0.90	0.020	0.035
b1	-	1.80	-	0.071
b2	0.95	1.45	0.037	0.057
c	0.46	0.76	0.018	0.030
c2	2.50	3.10	0.098	0.114
D	14.80	15.50	0.583	0.610
D1	2.40	3.20	0.094	0.126
D2	6.30	6.90	0.248	0.272
E	9.60	10.30	0.378	0.406
e1	4.95	5.20	0.195	0.205
L	12.60	13.80	0.496	0.543
L1	0.00	1.60	0.000	0.063
L4	-	4.10	-	0.161
P	3.00	3.40	0.118	0.134

MARKING DIAGRAM

P/N = Marking Code
G = Green Compound
YWW = Date Code
F = Factory Code

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Notice

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